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EDITORIAL

Changes to the Editorial Board	T.-J. K. Liu	4
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LETTERS

Silicon and Column IV Semiconductor Devices

A Dopingless FET With Metal–Insulator–Semiconductor Contacts	K.-H. Kao and L.-Y. Chen	5
Limitations on Lateral Nanowire Scaling Beyond 7-nm Node	U. K. Das, M. Garcia Bardon, D. Jang, G. Eneman, P. Schuddinck, D. Yakimets, P. Raghavan, and G. Groeseneken	9
Operation of SiGe HBTs Down to 70 mK	H. Ying, B. R. Wier, J. Dark, N. E. Lourenco, L. Ge, A. P. Omprakash, M. Mourigal, D. Davidovic, and J. D. Cressler	12
FinFET With Encased Air-Gap Spacers for High-Performance and Low-Energy Circuits	A. B. Sachid, Y.-M. Huang, Y.-J. Chen, C.-C. Chen, D. D. Lu, M.-C. Chen, and C. Hu	16

Compound Semiconductor Devices

Terahertz Heterodyne Communication Using GaAs Field-Effect Transistor Receiver	S. Blin, P. Nouvel, A. Pénarier, and J. Hesler	20
--	--	----

Memory Devices and Technology

Coupling-Shielded Inductor for High Isolation Between PA and LC-Based DCO	S.-S. Yoo, K.-Y. Lee, and H.-J. Yoo	24
Volatility Characterization for RRAM Devices	I. Gupta, A. Serb, R. Berdan, A. Khiat, and T. Prodromakis	28
Short Time High-Resistance State Instability of TaOx-Based RRAM Devices	X. Li, H. Wu, B. Gao, N. Deng, and H. Qian	32
Dual-Gate Charge Trap Flash Memory for Highly Reliable Triple Level Cell Using Capacitive Coupling Effects	M.-J. Ahn and W.-J. Cho	36
Low-Frequency Noise Characteristics in SONOS Flash Memory With Vertically Stacked Nanowire FETs	T. Bang, B.-H. Lee, C.-K. Kim, D.-C. Ahn, S.-B. Jeon, M.-H. Kang, J.-S. Oh, and Y.-K. Choi	40
Charge Trap Transistor (CTT): An Embedded Fully Logic-Compatible Multiple-Time Programmable Non-Volatile Memory Element for High- <i>k</i> -Metal-Gate CMOS Technologies	F. Khan, E. Cartier, J. C. S. Woo, and S. S. Iyer	44
Electric Field Induced Nitride Trapped Charge Lateral Migration in a SONOS Flash Memory	Y.-H. Liu, C.-M. Jiang, W.-C. Chen, T. Wang, W.-J. Tsai, T.-C. Lu, K.-C. Chen, and C.-Y. Lu	48

Thin-Film Transistors

“Driving”-Stress-Induced Degradation in Polycrystalline Silicon Thin-Film Transistors and Its Suppression by a Bridged-Grain Structure	M. Zhang, W. Zhou, R. Chen, M. Wong, and H.-S. Kwok	52
--	---	----

Optoelectronics, Display, Imaging

Suppression of Persistent Photoconductivity in AlGaN/GaN Ultraviolet Photodetectors Using <i>In Situ</i> Heating	M. Hou, H. So, A. J. Suria, A. S. Yalamarthy, and D. G. Senesky	56
A Tunable Dynamic Range Digital Single Photon Avalanche Diode	M. H. U. Habib and N. McFarlane	60
Fully Depleted Pinned Photodiode CMOS Image Sensor With Reverse Substrate Bias	K. D. Stefanov, A. S. Clarke, and A. D. Holland	64

(Contents Continued on Page 2)



A PUBLICATION OF THE IEEE ELECTRON DEVICES SOCIETY



Photosensitive Full-Swing Multi-Layer MoS ₂ Inverters With Light Shielding Layers	J. H. Ryu, G.-W. Baek, S. J. Yu, S. G. Seo, and S. H. Jin	67
Saturation Behavior for a Comb-Like Light-Induced Synaptic Transistor	G. Zhu, X. Gao, Y. Li, J. Yuan, W. Yuan, Y. Yang, Z. Zhang, and Y. Wang	71
Theoretical Investigation of Efficient Green Tunnel-Junction Light-Emitting Diodes	Y.-K. Kuo, Y.-H. Shih, J.-Y. Chang, F.-M. Chen, M.-L. Lee, and J.-K. Sheu	75
Self-Powered UV-B Photodetector Based on Hybrid Al:MgZnO/PEDOT:PSS Schottky Diode	Q. Zheng, J. Huang, C. Han, and Y. Chen	79
Solid-State Power and High-Voltage Devices		
High-Voltage and Low-Leakage AlGaN/GaN Tri-Anode Schottky Diodes With Integrated Tri-Gate Transistors	J. Ma and E. Matioli	83
Diamond Schottky Barrier Diodes With NO ₂ Exposed Surface and RF-DC Conversion Toward High Power Rectenna	T. Oishi, N. Kawano, S. Masuya, and M. Kasu	87
Integration of Gate Recessing and <i>In Situ</i> Cl ⁻ Doped Al ₂ O ₃ for Enhancement-Mode AlGaN/GaN MOSHEMTs Fabrication	H.-Y. Liu, C.-W. Lin, W.-C. Hsu, C.-S. Lee, M.-H. Chiang, W.-C. Sun, S.-Y. Wei, and S.-M. Yu	91
Novel Asymmetric Slant Field Plate Technology for High-Speed Low-Dynamic Ron E/D-mode GaN HEMTs	J. Wong, K. Shinohara, A. L. Corrion, D. F. Brown, Z. Carlos, A. Williams, Y. Tang, J. F. Robinson, I. Khalaf, H. Fung, A. Schmitz, T. Oh, S. Kim, S. Chen, S. Burnham, A. Margomenos, and M. Micovic	95
Investigation of the p-GaN Gate Breakdown in Forward-Biased GaN-Based Power HEMTs	A. N. Tallarico, S. Stoffels, P. Magnone, N. Posthuma, E. Sangiorgi, S. Decoutere, and C. Fiegnan	99
High-Performance Depletion/Enhancement-Mode β -Ga ₂ O ₃ on Insulator (GOOI) Field-Effect Transistors With Record Drain Currents of 600/450 mA/mm	H. Zhou, M. Si, S. Alghamdi, G. Qiu, L. Yang, and P. D. Ye	103
Balanced MSM-2DEG Varactors Based on AlGaN/GaN Heterostructure With Cutoff Frequency of 1.54 THz	J. H. Hwang, K.-J. Lee, S.-M. Hong, and J.-H. Jang	107
A 650 V Super-Junction MOSFET With Novel Hexagonal Structure for Superior Static Performance and High BV Resilience to Charge Imbalance: A TCAD Simulation Study	J. Park and J.-H. Lee	111
Materials, Processing, and Packaging		
Via Resistance Reduction in Advanced Copper Interconnects	C.-C. Yang, T. Spooner, P. McLaughlin, R. Quon, T. Standaert, and D. Edelstein	115
Method to Determine the Root Cause of Low- κ SiCOH Dielectric Failure Distributions	S. P. Ogden, K. B. Yeap, T. Shen, P. Justison, T.-M. Lu, and J. L. Plawsky	119
Sensors and Actuators		
Temperature Interference Reduction for Pressure Sensor Made of Conductive Polymer Composite	L. Wang	123
Vacuum Electron Devices		
W-Band Traveling Wave Tube Amplifier Based on Planar Slow Wave Structure	G. Ulisse and V. Krozer	126
Emerging Technologies and Devices		
Thickness Engineered Tunnel Field-Effect Transistors Based on Phosphorene	F. W. Chen, H. Ilatikhameneh, T. A. Ameen, G. Klimeck, and R. Rahman	130
First Principles Investigation of Small Molecules Adsorption on Antimonene	R.-S. Meng, M. Cai, J.-K. Jiang, Q.-H. Liang, X. Sun, Q. Yang, C.-J. Tan, and X.-P. Chen	134
Performance of Topological Insulator Interconnects	T. M. Philip, M. R. Hirsbrunner, M. J. Park, and M. J. Gilbert	138
Impact of Parasitic Capacitance and Ferroelectric Parameters on Negative Capacitance FinFET Characteristics	S. Khandelwal, J. P. Duarte, A. I. Khan, S. Salahuddin, and C. Hu	142
AIN/BP Heterostructure Photocatalyst for Water Splitting	Q. Yang, C.-J. Tan, R.-S. Meng, J.-K. Jiang, Q.-H. Liang, X. Sun, D.-G. Yang, and X.-P. Chen	145
CORRESPONDENCE		
Corrections to “AlGaN/GaN HEMTs With Damage-Free Neutral Beam Etched Gate Recess for High-Performance Millimeter-Wave Applications”	Y.-K. Lin, S. Noda, H.-C. Lo, S.-C. Liu, C.-H. Wu, Y.-Y. Wong, Q. H. Luc, P.-C. Chang, H.-T. Hsu, S. Samukawa, and E. Y. Chang	149

(Contents Continued from Page 2)

IEEE ELECTRON DEVICES SOCIETY MEETINGS CALENDAR	150
Information for Authors	153
ANNOUNCEMENTS	
Call for Papers—2017 1st Electron Devices Technology and Manufacturing Conference (EDTM)	154
About the Cover: Illustration of a light-wavelength-sensitive inverter circuit comprising two MoS ₂ thin-film transistors, with a light-shielding layer over only the driver device, by J. H. Ryu <i>et al.</i> , p. 67.	